

3SK272

GaAs N-Channel MES FET

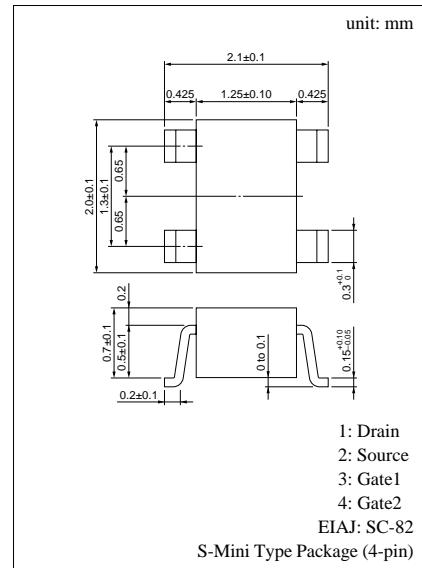
For VHF-UHF amplification

■ Features

- Low noise-figure (NF)
- Large power gain PG
- S-mini type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Drain to Source voltage	V _{DS}	13	V
Gate 1 to Source voltage	V _{G1S}	-6	V
Gate 2 to Source voltage	V _{G2S}	-6	V
Drain current	I _D	50	mA
Gate 1 current	I _{G1}	1	mA
Gate 2 current	I _{G2}	1	mA
Allowable power dissipation	P _D	150	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I _{PS}	V _{DS} = 5V, V _{G1S} = 0, V _{G2S} = 0	8.5		35	mA
Gate 2 to Drain current	I _{G2DO}	V _{G2D} = -13V (G1, S = Open)			50	μA
Gate 1 cut-off current	I _{G1SS}	V _{DS} = V _{G2S} = 0, V _{G1S} = -6V			-20	μA
Gate 2 cut-off current	I _{G2SS}	V _{DS} = V _{G1S} = 0, V _{G2S} = -6V			-20	μA
Drain cut-off current	I _{PSX}	V _{DS} = 13V, V _{G1S} = -3.5V, V _{G2S} = 0			50	μA
Gate 1 to Source cut-off voltage	V _{G1SC}	V _{DS} = 5V, V _{G2S} = 0, I _D = 200μA			-3.5	V
Gate 2 to Source cut-off voltage	V _{G2SC}	V _{DS} = 5V, V _{G1S} = 0, I _D = 200μA			-3.5	V
Forward transfer admittance	Y _{fs}	V _{DS} = 5V, I _D = 10mA, V _{G2S} = 1.5V, f = 1kHz	18	23		mS
Input capacitance (Common Source)	C _{iss}	V _{DS} = 5V, V _{G1S} = V _{G2S} = -6V f = 1MHz		0.4	2	pF
Output capacitance (Common Source)	C _{oss}			0.3	1.2	pF
Reverse transfer capacitance (Common Source)	C _{rss}			0.02	0.04	pF
Power gain	PG	V _{DS} = 5V, I _D = 10mA V _{G2S} = 1.5V, f = 800MHz	10	16		dB
Noise figure	NF			1.8	2.8	dB
Gain reduction	G _R	V _{DS} = 5V, V _{AGC} = 1.5V/-3.5V, f = 800MHz	37	45		dB

